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(71) Applicants (for all designated States except US): **ASML
US, INC.** [US/US]; 440 Kings Village Road, Scotts Valley,
CA 95066 (US). **INTEGRATED PROCESS SYSTEMS
LTD** [KR/KR]; 33 Jije-dong, Pyunglaek, Kyungkl-do
(KR).

(72) Inventors; and

(75) Inventors/Applicants (for US only): **LEE, Sang-In**

[KR/US]; 22608 San Juan Road, Cupertino, CA 95014
(US). **SENZAKI, Yoshihide** [JP/US]; 400 Clubhouse
Drive, Aptos, CA 95003 (US). **LEE, Sang-Kyoo** [KR/KR];
#201, 17-22 Yangjae 1 Dong, Suhcho-Gu, Seoul (KR).

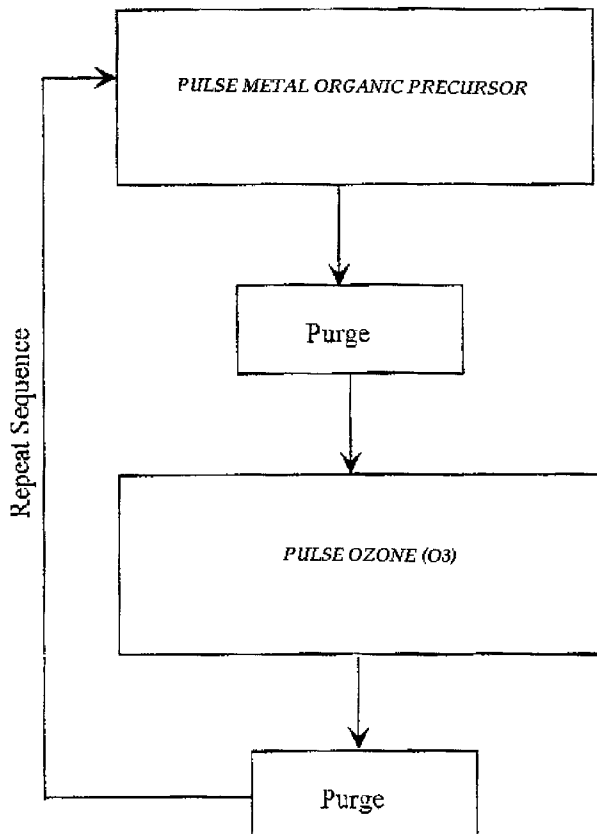
(74) Agents: **SWIATEK, Maria, S.** et al.; Dorsey & Whitney
LLP, 4 Embarcadero Center, Suite 3400, San Francisco, CA
94111 (US).

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(54) Title: ATOMIC LAYER DEPOSITION OF HIGH K METAL OXIDES



(57) Abstract: The present invention relates to the atomic layer deposition ("ALD") of high k dielectric layers of metal oxides containing Group 4 metals, including hafnium oxide, zirconium oxide, and titanium oxide. More particularly, the present invention relates to the ALD formation of Group 4 metal oxide films using an metal alkyl amide as a metal organic precursor and ozone as a co-reactant.

WO 2004/017377 A2



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